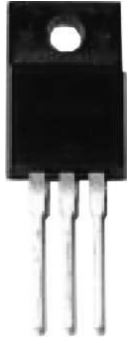
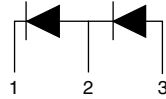


Hyperfast Rectifier, 15 A



3L TO-220 FULL-PAK



FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Designed and qualified for industrial level



RoHS
COMPLIANT

DESCRIPTION

15STH06FP 600 V series are the state of the art tandem hyperfast recovery rectifiers: excellent switching performance and extremely low forward voltage drop trade off is overcome, boosting overall application performance.

Specially designed for CCM PFC application, these devices show incomparable performance in every current intensive hard switching application.

Optimized reverse recovery stored charge enables reverse recovery stored charge enables downsizing of boosting switch and cooling system, increased operating frequency make possible use of smaller reactive elements. Cost effective PFC application is then possible with high efficiency over wide input voltage range and loading factor.

Plastic insulated package features easy mounting together with not insulated parts.

PRODUCT SUMMARY

t_{rr}	20 ns
$I_{F(AV)}$	15 A
V_R	600 V

ABSOLUTE MAXIMUM RATINGS FOR BOTH DIODES

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Repetitive peak reverse voltage	V_{RRM}		600	V
DC forward current	I_F	$T_C = 73\text{ }^\circ\text{C}$	15	A
Non-repetitive peak surge current	I_{FSM}	$T_C = 25\text{ }^\circ\text{C}$	115	
Operating junction and storage temperatures	T_J, T_{Stg}		- 55 to 175	$^\circ\text{C}$

ELECTRICAL SPECIFICATIONS FOR BOTH DIODES ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_r	$I_R = 100\text{ }\mu\text{A}$	600	-	-	V
Forward voltage	V_F	$I_F = 15\text{ A}$	-	2.2	2.4	
		$I_F = 15\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	1.9	2.1	
		$I_F = 15\text{ A}, T_J = 150\text{ }^\circ\text{C}$	-	1.8	2	
Reverse leakage current	I_R	$V_R = V_R\text{ rated}$	-	< 1	10	μA
		$T_J = 125\text{ }^\circ\text{C}, V_R = V_R\text{ rated}$	-	10	100	
		$T_J = 150\text{ }^\circ\text{C}, V_R = V_R\text{ rated}$	-	40	200	
Junction capacitance	C_T	$V_R = 600\text{ V}$	-	17	-	pF

DYNAMIC RECOVERY CHARACTERISTICS FOR BOTH DIODES ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t_{rr}	$I_F = 1.0\text{ A}$, $di_F/dt = -50\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$		-	-	28	ns
		$T_J = 25\text{ }^\circ\text{C}$	$I_F = 15\text{ A}$ $di_F/dt = -200\text{ A}/\mu\text{s}$ $V_R = 390\text{ V}$	-	20	-	
		$T_J = 125\text{ }^\circ\text{C}$		-	45	-	
Peak recovery current	I_{RRM}	$T_J = 25\text{ }^\circ\text{C}$	$I_F = 15\text{ A}$ $di_F/dt = -200\text{ A}/\mu\text{s}$ $V_R = 390\text{ V}$	-	2.6	-	A
		$T_J = 125\text{ }^\circ\text{C}$		-	5.6	6.5	
Reverse recovery charge	Q_{rr}	$T_J = 25\text{ }^\circ\text{C}$	$I_F = 15\text{ A}$ $di_F/dt = -200\text{ A}/\mu\text{s}$ $V_R = 390\text{ V}$	-	28	-	nC
		$T_J = 125\text{ }^\circ\text{C}$		-	140	-	

THERMAL - MECHANICAL SPECIFICATIONS FOR BOTH DIODES							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}			- 55	-	175	$^\circ\text{C}$
Thermal resistance, junction to case	R_{thJC}			-	-	3.9	$^\circ\text{C}/\text{W}$
Thermal resistance, case to heatsink	R_{thCS}	Mounting surface, flat, smooth and greased		-	0.2	-	
Weight				-	2.0	-	g
				-	0.07	-	oz.
Mounting torque				6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)

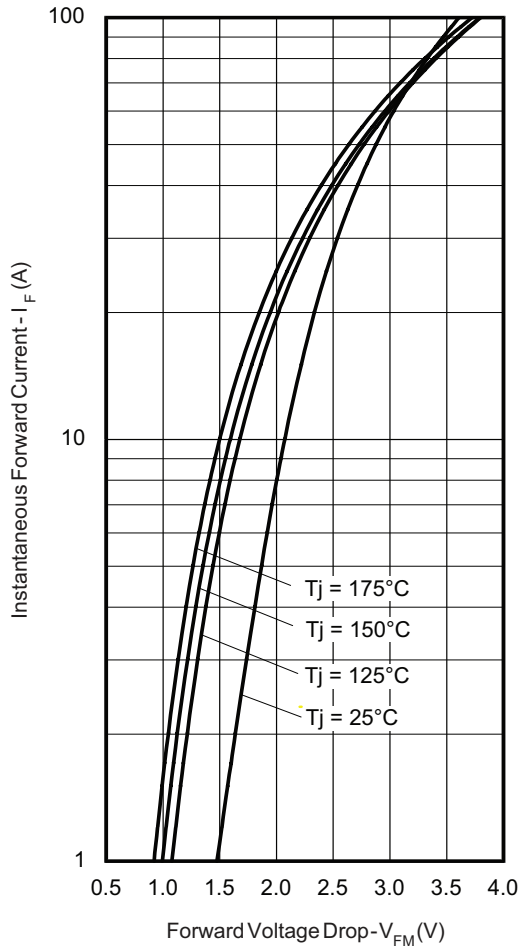


Fig. 1 - Maximum Forward Voltage Drop Characteristics

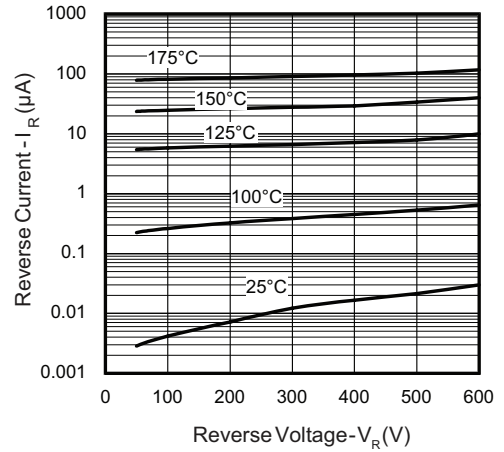


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

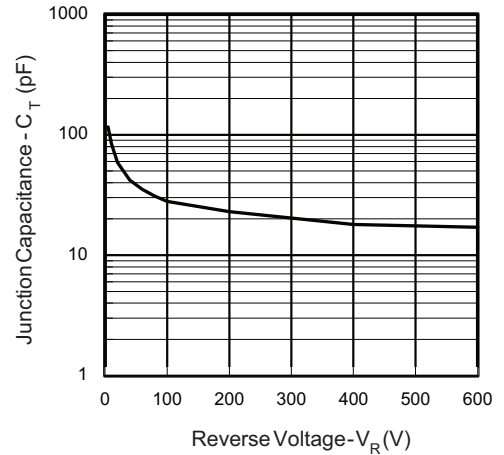


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

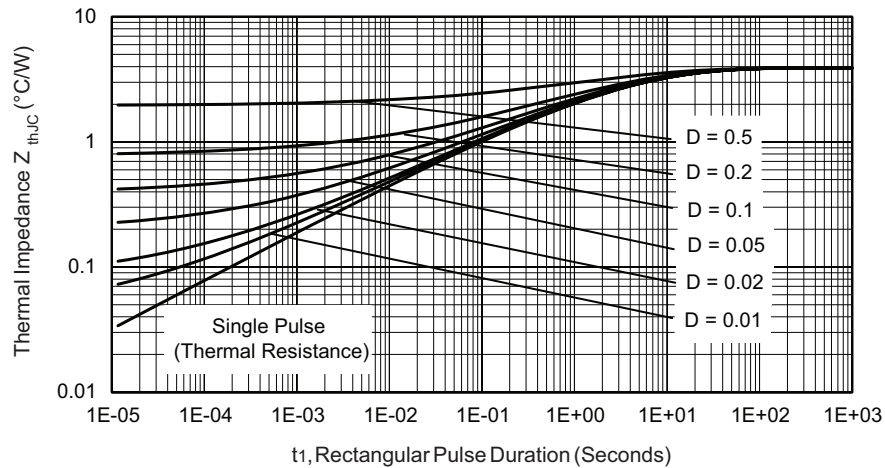


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

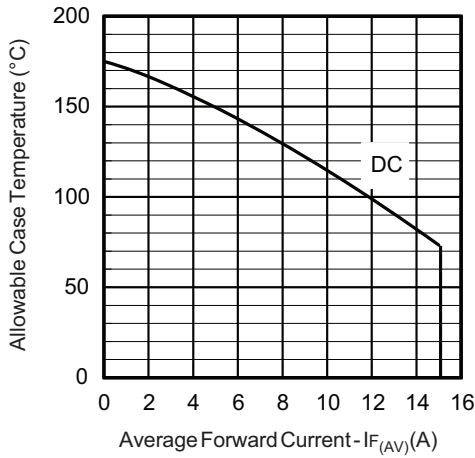


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

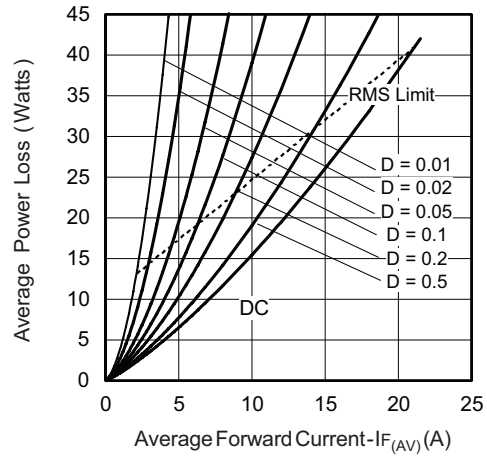


Fig. 6 - Forward Power Loss Characteristics

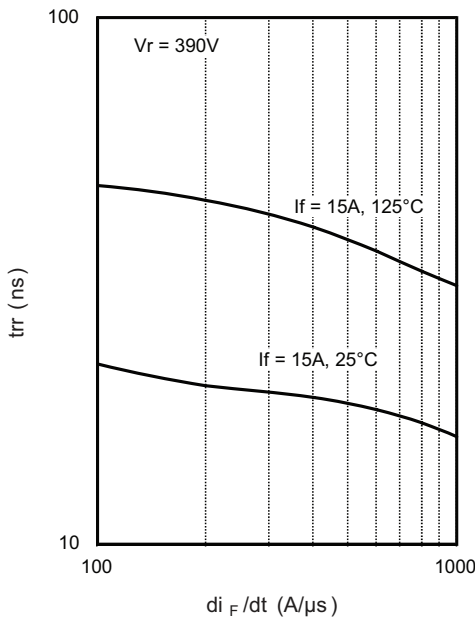


Fig. 7 - Typical Reverse Recovery Time vs. di_F/dt

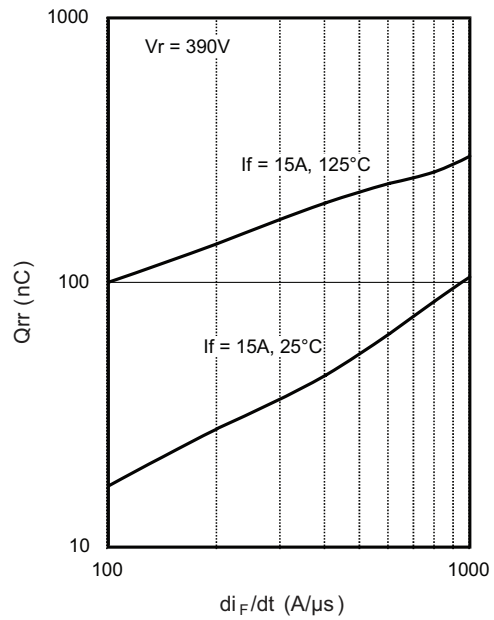


Fig. 8 - Typical Stored Charge vs. di_F/dt

LINKS TO RELATED DOCUMENTS

Dimensions	http://www.vishay.com/doc?95264
Part marking information	http://www.vishay.com/doc?95266



Notice

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